

Docket No.: 248760US0RD CONT

OBLON
SPIVAK
MCCLELLAND
MAIER
NEUSTADT
P.C.

ATTORNEYS AT LAW

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

RE: Application Serial No.: 10/773,297

Applicants: Yasuo OHBA Filing Date: February 9, 2004

For: NITRIDE COMPOUND SEMICONDUCTOR

ELEMENT Group Art Unit: 2822

Examiner: SOWARD, IDA M.

SIR:

Attached hereto for filing are the following papers:

Response Under 37 C.F. R. §1.312

Page 1 of Form PTO-1449 from IDS filed February 9, 2004, and Date-Stamped filing Receipt Reference Designated "AW" in IDS Filed February 9, 2004
Form PTO-1449 Date-Stamped August 22, 2002, from Parent 10188,744

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,

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Customer Number

22850

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

YASUO OHBA : EXAMINER: SOWARD, IDA M.

SERIAL NO: 10/773,297 : GROUP ART UNIT: 2822

FILED: FEBRUARY 9, 2004 : ALLOWED: JULY 31, 2006

FOR: NITRIDE COMPOUND SEMICONDUCTOR ELEMENT

RESPONSE UNDER 37 C.F.R. § 1.312

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313-1450

SIR:

Further to the Notice of Allowance dated July 31, 2006, Applicants respectfully request that the Examiner acknowledge consideration of the AW reference cited in the Information Disclosure Statement filed February 9, 2004, by appropriately initialing page 1 of the associated Form PTO-1449. For the Examiner's convenience a copy of page 1 of the Form PTO-1449 from the IDS filed February 9, 2004, is attached.

A copy of the AW reference filed February 9, 2004, is also attached.

The AW reference was considered by the Examiner in parent U.S. Application No. 10/188,744. See attached Form PTO-1449 date-stamped August 22, 2002, from 10/188,744 (downloaded from Public PAIR). As noted in M.P.E.P. § 609:

The examiner will consider information which has been considered by the Office in a parent application when examining (A) a continuation application filed Under 37 CFR 1.53(b) M.P.E.P. § 609.02.A.2, page 600-143, column 2.

There are exceptions to this requirement that a copy of the information must be provided. First, 37 CFR 1.98(d) states that a copy of any patent,

Application No. 10/773,297 Response Under 37 C.F.R. § 1.312

publication, pending U.S.-application,-or-other information listed in an information disclosure statement is not required to be provided if: (A) the information was previously cited by or submitted to, the Office in a prior application, provided that the prior application is properly identified in the IDS and is relied on for an earlier filing date under 35 U.S.C. 120; and (B) the IDS submitted in the earlier application complies with 37 CFR 1.98(a)-(c). If both of these conditions are met, the examiner will consider the information previously cited or submitted to the Office and considered by the Office in a prior application relied on under 35 U.S.C. 120. M.P.E.P. § 609.04(a).II, page 600-147, column 2.

Because both of these conditions are met, Applicants respectfully request that the Examiner acknowledge consideration of the AW reference in the above-identified application.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C. Norman F. Oblon

Corwin P. Umbach, Ph.D. Registration No. 40,211

Attached:

Page 1 of Form PTO-1449 from IDS filed February 9, 2004, and date-stamped filing receipt Reference designated "AW" in IDS filed February 9, 2004 Form PTO-1449 date-stamped August 22, 2002, from parent 10/188,744

Customer Number

22850

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OSMM&N File No. 248760USORD CONT

Serial No. ____

In the matter of the Application of: Yasuo OHBA

For: NITRIDE COMPOUND SEMICONDUCTOR ELEMENT

Due Date: FEBRUARY 8, 2004

Dept.: <u>CHEMICAL</u>

By: <u>NFO/CPU/wmb</u>

The following has been received in the U.S. Patent Office on the date stamped hereon:

- 30 pp. Specification 20 Claims/Drawings 8 Sheets and 2 Pages Application Data Sheet
- Combined Declaration, Petition & Power of Attorney 3 Pages
- Utility Patent Application Transmittal
- Request for Priority
- Check for \$770.00

Dep. Acct. Order Form

- Fee Transmittal Form
- Information Disclosure Statement
- PTO-1449 (3)
- White Advance Serial Number Card
- Preliminary Amendment (7 pp.)



AUG 2 4 2006

SHEET 1 OF

SERIAL NO. ATTY DOCKET NO. S DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Form PTO 1449 (Modified) 10/188,744 225255US0RD APPLICANT Yasuo OHBA LIST OF REFERENCES CITED BY APPLICANT **GROUP** FILING DATE 2811 July 5, 2002 U.S. PATENT DOCUMENTS **FILING DATE** SUB DOCUMENT CLASS **EXAMINER** IF APPROPRIATE DATE CLASS NUMBER INITIAL Y. OHBA, et al. 06/05/2001 6,242,764 AA Y. OHBA 11/23/99 AB 5,990,495 Y. OHBA, et al. 08/12/97 5,656,832 AC Y. OHBA, et al. 06/01/99 AD 5,909,040 07/27/99 Y. OHBA, et al. ΑE 5,929,466 AF AG AH ΑI AJ AK AL AM AN FOREIGN PATENT DOCUMENTS **TRANSLATION** DOCUMENT COUNTRY DATE NO YES NUMBER Х JAPAN (with English Abstract) 01/28/2000 2000-31588 ΑO AP AQ AR AS ΑT ΑU ΑV OTHER REFERENCES (Including Author, Title, Date, Perlinent Pages, etc.) Y. OHBA, et al., Japanese Journal of Applied Physics, Vol. 37 Part 2, No. 8A, pps. L 905-L 906, *FABRICATION AND CHARACTERIZATION OF AIGAN/GAN DOUBLE-HETEROLASER STRUCTURES ON SAPPHIRE SUBSTRATES USING SINGLE CRYSTALLINE AIN BUFFER LAYERS,* August 1, 1998 AW AX AY Additional References sheet(s) attached 02/05/03. **Date Considered** Examiner *Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EXAMINER INITIAL AA A AB A AC A AD A AF A AG AH AI AJ AK AL AM	NCES CITED BY A		APPLICANT \2		248760US0RDCONT AUG 2 4 2006 New Continuation of 10/188,744		
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AA AA AAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
AB AC AC AD AE AF AG AH AI AJ AK AL AM AN AN	4,792,958	12/20/88	OHBA, et al.				
AC AD AD AE AF AG AH AI AJ AK AL AM AN AN	4,809,287	02/28/89	OHBA, et al.				
AD AE AE AF AG AH AI AJ AK AL AM AN AN	4,835,117	05/30/89	OHBA, et al.				
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	5,103,271	04/07/92	IZUMIYA, et al.				
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	DOCUMENT NUMBER	DATE	COUNTRY		TRANSLATION YES NO		
AP	2000-31588	01/28/00	JAPAN				
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AW		IONION AIGS AND	of Applied Physics, Vol. 37 Part 2, No. GaN DOUBLE-HETEROLASER STRL FER LAYERS," August 1, 1998.	CTURES C	N SAPPHI	RE SUBSTRATES USIN	
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